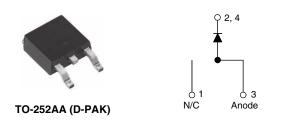
HEXFRED[®] Ultrafast Soft Recovery Diode, 4 A



PRODUCT SUMMARY									
Package	TO-252AA (D-PAK)								
I _{F(AV)}	4 A								
V _R	600 V								
V _F at I _F	1.4 V								
t _{rr} typ.	17 ns								
T _J max.	150 °C								
Diode variation	Single die								

FEATURES

- Ultrafast recovery time
- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- Guaranteed avalanche
- Specified at operating temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION / APPLICATIONS

These diodes are optimized to reduce losses and EMI / RFI in high frequency power conditioning systems. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for freewheeling, flyback, power converters, motor drives, and other applications where high speed and reduced switching losses are design requirements.

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Cathode to anode voltage	V _{RRM}		600	V						
Maximum continuous forward current	I _{F(AV)}	T _C = 100 °C	4							
Single pulse forward current	I _{FSM}		25	A						
Repetitive peak forward current	I _{FRM}	T _C = 116 °C	16							
Maximum power dissipation	PD	T _C = 100 °C	10	W						
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +150	°C						

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-				
Forward voltage See fig. 1	V _F	$I_F = 4 A$		1.5	1.8	V			
		I _F = 8 A	-	1.8	2.2				
		I _F = 4 A, T _J = 125 °C	-	1.4	1.7				
Maximum reverse		$V_{R} = V_{R}$ rated	-	0.17	3.0				
leakage current	I _R	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	-	44	300	μA			
Junction capacitance	CT	V _R = 200 V	-	4	8	pF			
Series inductance	LS	Measured lead to lead 5 mm from package body	-	8.0	-	nH			

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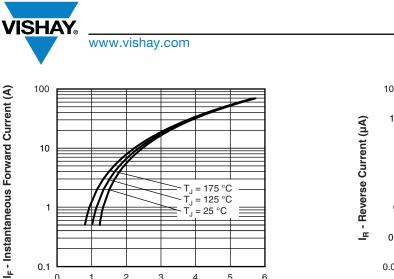


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DYNAMIC RECOVERY CHARACTERISTICS ($T_C = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 1.0 \text{ A}$	200 A/µA, V _R = 30 V	-	17	-			
Reverse recovery time	t _{rr}	T _J = 25 °C		-	28	42	ns		
		T _J = 125 °C	I _F = 4 A dI _F /dt = 200 A/μs V _R = 200 V	-	38	57			
Deals receivers ourrent	I _{RRM}	T _J = 25 °C		-	2.9	5.2	A		
Peak recovery current		T _J = 125 °C		-	3.7	6.7			
	Q _{rr}	T _J = 25 °C		-	40	60			
Reverse recovery charge		T _J = 125 °C		-	70	105	nC		
Rate of fall of recovery current	dl _{(rec)M} /dt	T _J = 25 °C		-	280	-			
		T _J = 125 °C		-	235	-	A/µs		

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	150	°C				
Thermal resistance, junction to case	R _{thJC}		-	-	5.0	°C/W				
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	C/W				
Weight			-	2.0	-	g				
weight			-	0.07	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style To-252AA (D-PAK)	HFA04SD60S							



= 175 °C

Т_. = 125 °С

= 25 °C Т

5

6

4

V_F - Forward Voltage Drop (V) Fig. 1 - Typical Forward Voltage Drop Characteristics

3

10

1

0.1

0

1

2

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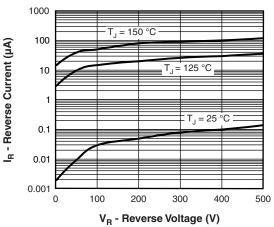


Fig. 2 - Typical Values of Reverse Current vs. **Reverse Voltage**

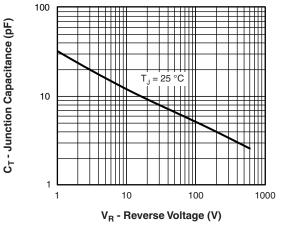


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

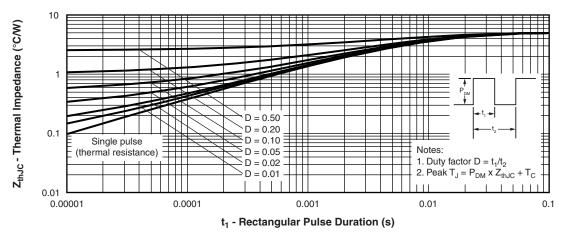


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

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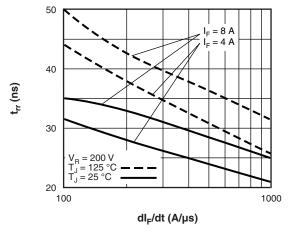
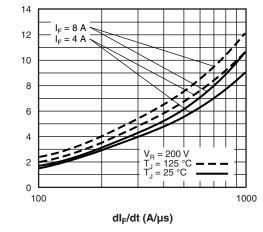


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt

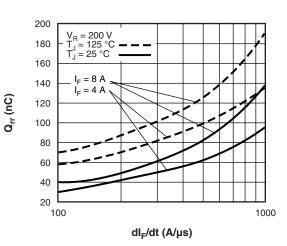


I_{RR} (A)

Fig. 6 - Typical Recovery Current vs. dl_F/dt

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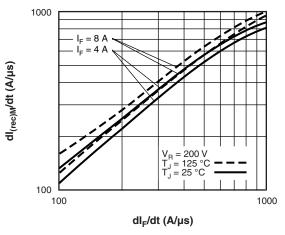


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt

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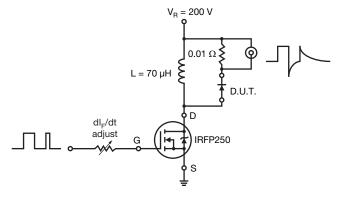
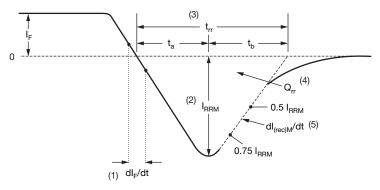


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (4) ${\rm Q}_{\rm rr}$ area under curve defined by ${\rm t}_{\rm rr}$ and ${\rm I}_{\rm RRM}$
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

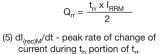


Fig. 10 - Reverse Recovery Waveform and Definitions

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Device code	VS-	HF	Α	04	SD	60	S	TR	PbF
		(2)	(3)	(4)	(5)	(6)	(7)	(8)	(9)
	 Vishay Semiconductors product HEXFRED[®] family Electron irradiated Current rating (04 = 4 A) D-PAK 								
	6 - Voltage rating (60 = 600 V)								
	7 - S = D-PAK 8 - • TR = tape and reel								
	 TRR = tape and reel (right oriented) TRL = tape and reel (left oriented) PbF = lead (Pb)-free P = lead (Pb)-free (for TRR and TRL) 								

LINKS TO RELATED DOCUMENTS							
Dimensions www.vishay.com/doc?95016							
Part marking information	www.vishay.com/doc?95059						
Packaging information	www.vishay.com/doc?95033						

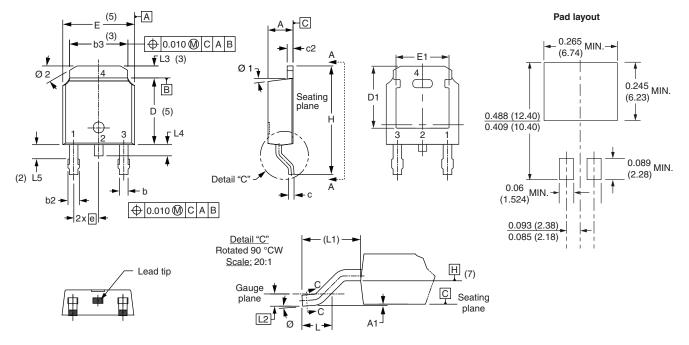






D-PAK (TO-252AA)

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	IETERS	INC	HES	NOTES	NOTES		MILLIN	IETERS	INC	HES	NOTES
STNIBOL	MIN.	MAX.	MIN.	MAX.	NUTES		SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
A	2.18	2.39	0.086	0.094			е	2.29	BSC	0.090) BSC	
A1	-	0.13	-	0.005			Н	9.40	10.41	0.370	0.410	
b	0.64	0.89	0.025	0.035			L	1.40	1.78	0.055	0.070	
b2	0.76	1.14	0.030	0.045			L1	2.74	BSC	0.108	REF.	
b3	4.95	5.46	0.195	0.215	3	L2 0.51 BSC 0.020 BSC		BSC				
с	0.46	0.61	0.018	0.024			L3	0.89	1.27	0.035	0.050	3
c2	0.46	0.89	0.018	0.035			L4	-	1.02	-	0.040	
D	5.97	6.22	0.235	0.245	5		L5	1.14	1.52	0.045	0.060	2
D1	5.21	-	0.205	-	3		Ø	0°	10°	0°	10°	
E	6.35	6.73	0.250	0.265	5]	Ø1	0°	15°	0°	15°	
E1	4.32	-	0.170	-	3		Ø2	25°	35°	25°	35°	

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

(2) Lead dimension uncontrolled in L5

⁽³⁾ Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad

(4) Section C - C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip

(5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁶⁾ Dimension b1 and c1 applied to base metal only

⁽⁷⁾ Datum A and B to be determined at datum plane H

⁽⁸⁾ Outline conforms to JEDEC outline TO-252AA

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